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Annual Report 2010

Institute of Optoelectronics

Cover photo:

Free-standing GaN wafer with a thickness of about 1.5 mm grown by hydride vapor phase epitaxy (see articles on pages 55 and 63). The wafer was self-separated from the original sapphire substrate by the strain induced during cool-down owing to the different thermal expansion coefficients of GaN and sapphire, enforced by a hexagonally shaped mask interlayer.